

Features

Indium Gallium nitride based material
 Broad band UVA+UVB+UVC photodiode
 Photovoltaic mode operation
 TO-46 metal housing
 Good visible blindness
 High responsivity and low dark current



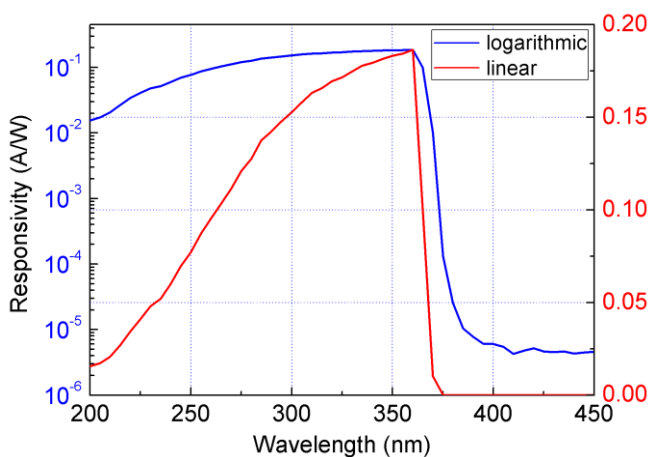
Applications

UV LED monitoring
 UV radiation dose measurement
 UV Curing

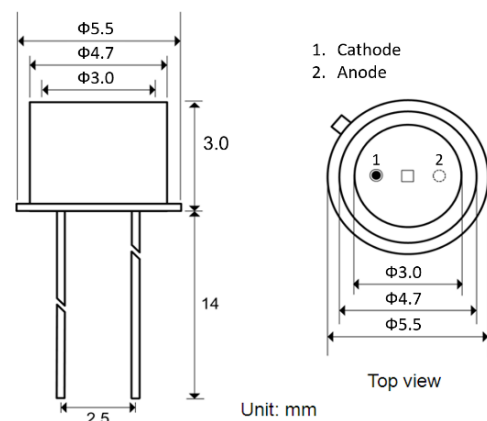
Specifications

| Parameter | Symbol | Value | Unit |
|--|-----------------|---------|-----------------|
| Spectral characteristics (25 °C) | | | |
| Wavelength of peak responsivity | λ_{max} | 360 | nm |
| Peak responsivity (at 360 nm) | R_{max} | 0.18 | A/W |
| Spectral response range | - | 180~370 | nm |
| UV/visible rejection ratio ($R_{max}/R_{400\text{ nm}}$) | VB | $>10^4$ | - |
| General characteristics (25 °C) | | | |
| Chip size | A | 1 | mm ² |
| Dark current (1 V reverse bias) | I_d | <1 | nA |
| Capacitance (at 0 V and 1 MHz) | C | 23 | pF |
| Temperature coefficient | T_c | -0.1 | %/°C |
| Maximum ratings | | | |
| Operation temperature range | T_{opt} | -40~85 | °C |
| Storage temperature range | T_{stor} | -40~85 | °C |
| Soldering temperature (3 s) | T_{sold} | 260 | °C |
| Reverse voltage | V_{Rmax} | 10 | V |

Spectral response



Package dimensions



***Caution:** ESD can damage the device hence please avoid ESD.